









SN74LVC1G123 SCES586E - JULY 2004 - REVISED MARCH 2024

SN74LVC1G123 Single Retriggerable Monostable Multivibrator With Schmitt-Trigger Inputs

1 Features

- Available in the Texas Instruments NanoFree[™] Package
- Supports 5V V_{CC} Operation
- Inputs Accept Voltages to 5.5V
- Max t_{pd} of 8ns at 3.3V
- Supports Mixed-Mode Voltage Operation on All Ports
- Supports Down Translation to V_{CC}
- Schmitt-Trigger Circuitry on A and B Inputs for Slow Input Transition Rates
- Edge Triggered From Active-High or Active-Low Gated Logic Inputs
- Retriggerable for Very Long Output Pulses, Up to 100% Duty Cycle
- Overriding Clear Terminates Output Pulse
- Glitch-Free Power-Up Reset on Outputs
- Ioff Supports Live Insertion, Partial-Power-Down Mode, and Back-Drive Protection
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- **ESD Protection Exceeds JESD 22**
 - 2000V Human-Body Model (A114-A)
 - 200V Machine Model (A115-A)
 - 1000V Charged-Device Model (C101)

2 Applications

- **AV Receivers**
- Blu-ray Players and Home Theaters
- **DVD Recorders and Players**
- Desktop PCs or Notebook PCs
- Digital Radio and Internet Radio Players
- Digital Video Cameras (DVC)
- Embedded PCs
- **GPS: Personal Navigation Devices**
- Mobile Internet Devices
- Network Attached Storage (NAS)
- Personal Digital Assistant (PDA)
- Server PSU
- Solid-State Drive (SSD): Client and Enterprise
- Video Analytics Servers
- Wireless Headsets, Keyboards, and Mice

3 Description

The SN74LVC1G123 device is a single retriggerable monostable multivibrator designed for 1.65V to 5.5V V_{CC} operation.

This monostable multivibrator features output pulseduration control by three methods. In the first method, the \overline{A} input is low, and the B input goes high. In the second method, the B input is high, and the \overline{A} input goes low. In the third method, the \overline{A} input is low, the B input is high, and the clear (\overline{CLR}) input goes high.

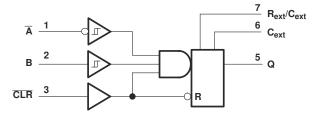
The output pulse duration is programmed by selecting external resistance and capacitance values. The external timing capacitor must be connected between C_{ext} and R_{ext}/C_{ext} (positive) and an external resistor connected between Rext/Cext and Vcc. To obtain variable pulse durations, connect an external variable resistance between Rext/Cext and Vcc. The output pulse duration also can be reduced by taking CLR low.

Pulse triggering occurs at a particular voltage level and is not directly related to the transition time of the input pulse. The \overline{A} and B inputs have Schmitt triggers with sufficient hysteresis to handle slow input transition rates with jitter-free triggering at the outputs.

Device Information

PART NUMBER	PACKAGE (1)	BODY SIZE (NOM)			
	SSOP (8)	2.95mm × 2.80mm			
SN74LVC1G123	VSSOP (8)	2.30mm × 2.00mm			
	DSBGA (8)	1.91mm × 0.91mm			

For all available packages, see the orderable addendum at the end of the data sheet.



Logic Diagram (Positive Logic)

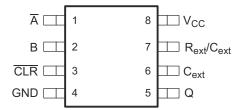


Table of Contents

1 Features	.1	7.1 Overview	12
2 Applications	.1	7.2 Functional Block Diagram	12
3 Description	.1	7.3 Feature Description	12
4 Pin Configuration and Functions	.3	7.4 Device Functional Modes	13
5 Specifications		8 Application and Implementation	14
5.1 Absolute Maximum Ratings	4	8.1 Application Information	
5.2 ESD Ratings		8.2 Typical Application	
5.3 Recommended Operating Conditions		9 Power Supply Recommendations	
5.4 Thermal Information	.5	10 Layout	
5.5 Electrical Characteristics	.5	10.1 Layout Guidelines	. 16
5.6 Timing Requirements	.6	10.2 Layout Example	
5.7 Switching Characteristics, C _L = 15 pF, –40°C to		11 Device and Documentation Support	
85°C	. 7	11.1 Documentation Support	
5.8 Switching Characteristics, C _L = 50 pF, –40°C to		11.2 Receiving Notification of Documentation Updates.	
85°C	7	11.3 Support Resources	. 17
5.9 Switching Characteristics, C _L = 50 pF, –40°C to		11.4 Trademarks	
125°C	.7	11.5 Electrostatic Discharge Caution	17
5.10 Operating Characteristics	8	11.6 Glossary	
5.11 Typical Characteristics	9	12 Revision History	
6 Parameter Measurement Information	10	13 Mechanical, Packaging, and Orderable	
7 Detailed Description	12	Information	18



4 Pin Configuration and Functions



See mechanical drawings for dimensions.

Figure 4-1. DCT Package 8-Pin SSOP Top View

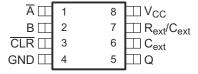


Figure 4-2. DCU Package 8-Pin VSSOP Top View

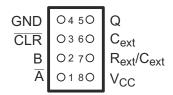


Figure 4-3. YZP Package 8-Pin DSBGA Bottom View

Table 4-1. Pin Functions

P	N	I/O	DESCRIPTION					
NAME	NO.	1/0	DESCRIPTION					
Ā	1	I	Falling edge sensitive input; requires B and CLR to be held high.					
В	2	I	Rising edge sensitive input; requires \overline{A} to be held low and \overline{CLR} to be held high.					
CLR	3	I	Clear, Active Low; also can operate as rising edge sensitive input if \overline{A} is held low and B is held high.					
GND	4	_	Ground					
Q	5	0	Output					
C _{ext}	6	_	Connects only to the external capacitor					
R _{ext} /C _{ext}	7	_	Connects to the external capacitor and resistor					
V _{CC}	8	_	Power					



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage		-0.5	6.5	V
VI	Input voltage ⁽²⁾		-0.5	6.5	V
Vo	Voltage applied to any output in the high-impeda	nce or power-off state ⁽²⁾	-0.5	6.5	V
Vo	Voltage applied to any output in the high or low s	-0.5	V _{CC} + 0.5	V	
I _{IK}	Input clamp current	V _I < 0		-50	mA
I _{OK}	Output clamp current	V _O < 0		-50	mA
Io	Continuous output current	·		±50	mA
	Continuous current through V _{CC} or GND			±100	mA
T _{stg}	Storage temperature		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

5.2 ESD Ratings

			VALUE	UNIT
		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾		
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	+1000	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
\/	Supply voltage	Operating	1.65	5.5	V
V _{CC}	Supply voltage	Data retention only	1.5		V
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}		
	High-level input voltage	V _{CC} = 2.3 V to 2.7 V	1.7		V
V _{IH}	rigii-level iliput voltage	V _{CC} = 3 V to 3.6 V	2		V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0.7 × V _{CC}		
		V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}	
V _{IL}	Low-level input voltage	V _{CC} = 2.3 V to 2.7 V		0.7	V
\ \IL	Low-level input voitage	V_{CC} = 3 V to 3.6 V		8.0	V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.3 × V _{CC}	
VI	Input voltage		0	5.5	V
Vo	Output voltage		0	V _{CC}	V
		V _{CC} = 1.65 V		-4	
		V _{CC} = 2.3 V		-8	
I _{OH}	High-level output current	V _{CC} = 3 V		-16	mA
	V _{CC} – 3 V			-24	
		V _{CC} = 4.5 V		-32	

⁽²⁾ The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

⁽³⁾ The value of V_{CC} is provided in the Recommended Operating Conditions table.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



5.3 Recommended Operating Conditions (continued)

over operating free-air temperature range (unless otherwise noted)(1)

			MIN M	AX UNIT
		V _{CC} = 1.65 V		4
I _{OL}	Low-level output current		8	
		V - 2 V		16 mA
		VCC - 3 V		24
		V _{CC} = 4.5 V		32
R _{ext} (2)	External timing registance	V _{CC} = 2 V	5	kΩ
R _{ext} (-)	External timing resistance	V _{CC} ≥ 3 V	1	K12
T _A	Operating free-air temperature		-40 ·	25 °C

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, SCBA004.

5.4 Thermal Information

	THERMAL METRIC ⁽¹⁾	DCT (SSOP)	DCU (VSSOP)	YZP (DSBGA)	UNIT
		8 PINS	8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	220	227	102	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

5.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

DADAMETED	TEST CONDIT	IONO V		–40°C	TO 85°C		-40°C	TO 125°C	;	UNIT
PARAMETER	TEST CONDIT	IONS Vo	c	MIN	TYP ⁽¹⁾	MAX	MIN	TYP ⁽¹⁾	MAX	UNII
	I _{OH} = -100 μA	1.65 5.5		V _{CC} - 0.1			V _{CC} - 0.1			
	I _{OH} = -4 mA	1.68	5 V	1.2			1.2			
V _{OH}	I _{OH} = -8 mA	2.3	5 V	1.9			1.9			V
	I _{OH} = -16 mA	2	3 V	2.4			2.4			
	I _{OH} = -24 mA	3	v [2.3			2.3			
	I _{OH} = -32 mA	4.5	4.5 V	3.8			3.8			
	I _{OL} = 100 μA	1.65 5.5				0.1			0.1	
	I _{OL} = 4 mA	1.69	5 V			0.45			0.45	
V _{OL}	I _{OL} = 8 mA	2.3	V			0.3			0.3	V
	I _{OL} = 16 mA	3	,			0.4			0.4	
	I _{OL} = 24 mA	3	<u> </u>			0.55			0.55	
	I _{OL} = 32 mA	4.5	5 V			0.55			0.55	
R _{ext} /C _{ext} (2)	$B = GND, \qquad \overline{A} = \overline{CL}$	R = V _{CC} 1.65				±0.25			±0.25	μA
Ā, B, CLR	V _I = 5.5 V or GND	5.5	5 V			±1			±1	μΛ
I_{off} \overline{A} , B, Q, \overline{CLR}	V _I or V _O = 5.5 V	C)			±10			±10	μΑ
I _{CC} Quiescent	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5	5 V			20			20	μΑ
,		1.68	5 V			165			165	
		2.3	V			220			220	
I _{CC} Active state	$V_I = V_{CC}$ or GND, R_{ext}/C_e	ext = 0.5 V _{CC} 3	V			280			280	μΑ
		4.5	V			650		•	650	
		5.5	V			975			975	

⁽²⁾ R_{ext}/C_{ext} is an I/O and must not be connected directly to GND or V_{CC} .



5.5 Electrical Characteristics (continued)

over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	Vcc	-40°C TO 85°C	-40°C TO 125°C	UNIT
		TEST CONDITIONS	VCC	MIN TYP ⁽¹⁾ MAX	MIN TYP ⁽¹⁾ MAX	UNII
	Cı	V _I = V _{CC} or GND	3.3 V	3		pF

- (1) All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
- (2) This test is performed with the terminal in the OFF-state condition.

5.6 Timing Requirements

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 6-1)

							-40°C TO 125°C						
PARAMETER		TEST CONDITIONS		V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT	
			1			MIN	TYP	MIN	TYP	MIN	TYP		
t _w IN Pulse duration				8		4		3		2.5		ns	
LWIIN	ruise duration	A or B trigger			8		4		3		2.5		115
			D - 1 kO	C _{ext} = 100 pF						5.5		4.5	ns
	Pulse retrigger time		$R_{\text{ext}} = 1 \text{ k}\Omega$	C _{ext} = 100 µF						1.4		1.1	μs
t _{rr} Pulse retrigger time			D - 5 kO	C _{ext} = 100 pF		75		45					ns
			$R_{\text{ext}} = 5 \text{ k}\Omega$	C _{ext} = 100 µF		1.8		1.4					μs

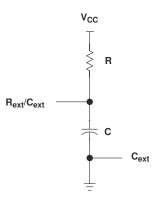


Figure 5-1. Required Timing Circuit

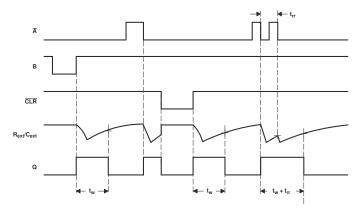


Figure 5-2. Input/Output Timing Diagram



5.7 Switching Characteristics, $C_L = 15 \text{ pF}, -40^{\circ}\text{C}$ to 85°C

over recommended operating free-air temperature range, C_L = 15 pF (unless otherwise noted) (see Figure 6-1)

		·	−40°C TO 85°C									
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V			V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
	Ā or B		7	18.5	52	4	17	3	11.5	2	7.6	
t _{pd}	CLR	Q	5	12.4	34	3	11.5	2	8	1.5	5.5	ns
	CLR trigger		7	17.4	54	4	15.5	3	10.5	2	7	

5.8 Switching Characteristics, $C_L = 50 \text{ pF}$, -40°C to 85°C

over recommended operating free-air temperature range, $C_1 = 50 \text{ pF}$ (unless otherwise noted) (see Figure 6-1)

				−40°C TO 85°C									
PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS		V _{CC} = 1.8 V ± 0.15 V			V _{CC} = 2.5 V ± 0.2 V		3.3 V 3 V	V _{CC} = 5 V ± 0.5 V		UNIT
				MIN	TYP ⁽¹⁾	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
	Ā or B			6	18.6	57	3	18.5	2	12.5	1.5	8.2	
t _{pd}	CLR	Q		4	11.6	36.5	2	12.5	1.5	8.6	1.5	6	ns
	CLR trigger			5	17.3	59	2.5	17	2	11.5	1.5	7.5	
			C_{ext} = 28 pF, R_{ext} = 2 k Ω		225	600	190	220	170	200	150	180	ns
t _w OUT ⁽²⁾		Q	$C_{\text{ext}} = 0.01 \mu\text{F},$ $R_{\text{ext}} = 10 \text{k}\Omega$		100	110	100	110	100	110	100	110	μs
			$C_{\text{ext}} = 0.1 \mu\text{F},$ $R_{\text{ext}} = 10 \text{k}\Omega$		1	1.1	1	1.1	1	1.1	1	1.1	ms

5.9 Switching Characteristics, C_L = 50 pF, -40°C to 125°C

over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 6-1)

				-40°C TO 125°C									
PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT	
				MIN	TYP ⁽¹⁾	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
	Ā or B			6		58	3	19.5	2	13.2	1.5	8.7	
t _{pd}	CLR	Q		4		37	2	13.5	1.5	9.2	1.5	6.5	ns
	CLR trigger			5		60	2.5	18	2	12	1.5	8	
			C_{ext} = 28 pF, R_{ext} = 2 k Ω		225	600	190	220	170	200	150	180	ns
t _w OUT ⁽²⁾		Q	$C_{\text{ext}} = 0.01 \mu\text{F},$ $R_{\text{ext}} = 10 \text{k}\Omega$		100	110	100	110	100	110	100	110	μs
			$C_{\text{ext}} = 0.1 \mu\text{F},$ $R_{\text{ext}} = 10 \text{k}\Omega$		1	1.1	1	1.1	1	1.1	1	1.1	ms

⁽¹⁾ $T_A = 25^{\circ}C$

 ⁽¹⁾ T_A = 25°C
 (2) t_w = Duration of pulse at Q output

⁽²⁾ t_w = Duration of pulse at Q output



5.10 Operating Characteristics

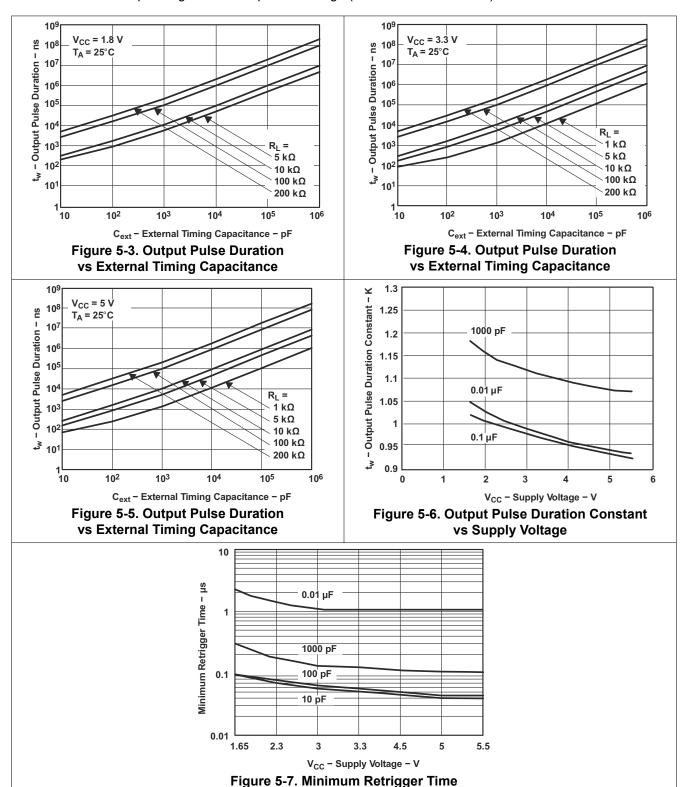
 $T_A = 25^{\circ}C$

1A 20 0										
	PARAMETER	TEST CONDITIONS		V _{CC} = 1.8 V	V_{CC} = 2.5 V	V _{CC} = 3.3 V	$V_{CC} = 5 V$	UNIT		
	PARAMETER	IESI CONI	DITIONS	TYP	TYP	TYP	TYP	UNIT		
C _{pd}	Power dissipation	\overline{A} = low, B = high,	R _{ext} = 1 kΩ, No C _{ext}			35	37	pF		
	capacitance	CLR = 10 MHz	$R_{ext} = 5 k\Omega,$ No C_{ext}	41	40			pr		



5.11 Typical Characteristics

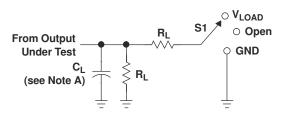
over recommended operating free-air temperature range (unless otherwise noted)



vs Supply Voltage



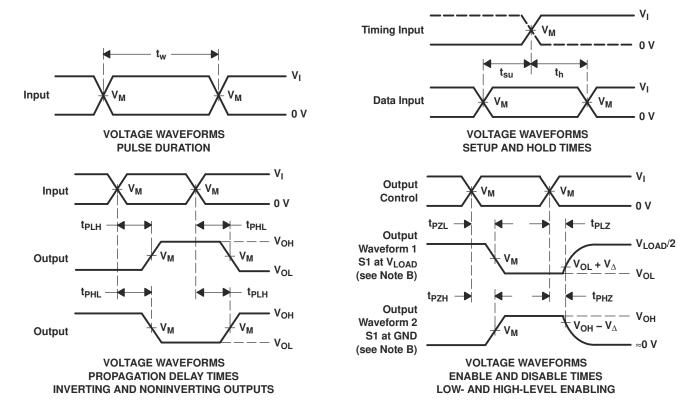
6 Parameter Measurement Information



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

LOAD	CIRCUIT	

V	INI	PUTS	.,	V			.,
V _{CC}	VI	t _r /t _f	V _M	V _{LOAD}	CL	RL	V_{Δ}
1.8 V \pm 0.15 V	V _{CC}	≤2 ns	V _{CC} /2	2×V _{CC}	15 pF	1 Μ Ω	0.15 V
2.5 V \pm 0.2 V	v_{cc}	≤2 ns	V _{CC} /2	2 × V _{CC}	15 pF	1 Μ Ω	0.15 V
3.3 V \pm 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	15 pF	1 Μ Ω	0.3 V
5 V \pm 0.5 V	v_{cc}	≤2.5 ns	V _{CC} /2	2 × V _{CC}	15 pF	1 Μ Ω	0.3 V

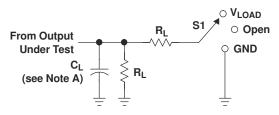


NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \ \Omega$.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en}.
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 6-1. Load Circuit and Voltage Waveforms

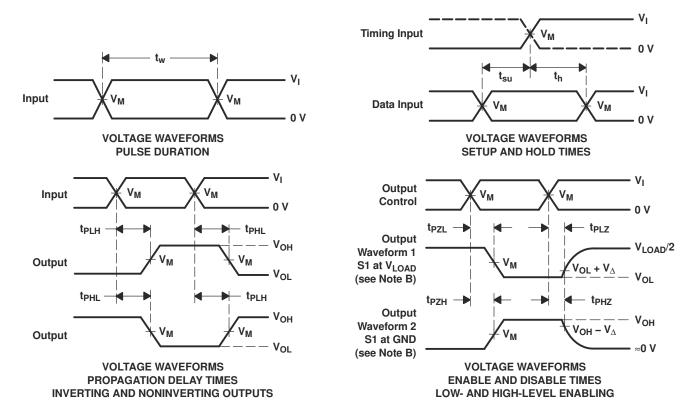




TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

LOAD CIRCUIT

V	INI	PUTS	V	V	0	В	V	
V _{CC}	V _I t _r /t _f		V _M	V _{LOAD}	CL	R _L	V_{Δ}	
1.8 V \pm 0.15 V	V _{CC}	≤2 ns	V _{CC} /2	2×V _{CC}	30 pF	1 k Ω	0.15 V	
2.5 V \pm 0.2 V	V_{CC}	≤2 ns	V _{CC} /2	2 × V _{CC}	30 pF	500 Ω	0.15 V	
3.3 V \pm 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V	
5 V \pm 0.5 V	V_{CC}	≤2.5 ns	V _{CC} /2	2 × V _{CC}	50 pF	500 Ω	0.3 V	



- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50~\Omega$.
 - D. The outputs are measured one at a time, with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
 - F. t_{PZL} and t_{PZH} are the same as t_{en}.
 - G. t_{PLH} and t_{PHL} are the same as t_{pd} .
 - H. All parameters and waveforms are not applicable to all devices.

Figure 6-2. Load Circuit and Voltage Waveforms

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7 Detailed Description

7.1 Overview

The SN74LVC1G123 device is a single retriggerable monostable multivibrator designed for 1.65-V to 5.5-V V_{CC} operation.

This monostable multivibrator features output pulse-duration control by three methods. In the first method, the \overline{A} input is low, and the \overline{B} input goes high. In the second method, the \overline{B} input is high, and the \overline{A} input goes low. In the third method, the \overline{A} input is low, the \overline{B} input is high, and the clear (\overline{CLR}) input goes high.

The output pulse duration is programmed by selecting external resistance and capacitance values. The external timing capacitor must be connected between C_{ext} and R_{ext}/C_{ext} (positive) and an external resistor connected between R_{ext}/C_{ext} and V_{CC} . To obtain variable pulse durations, connect an external variable resistance between R_{ext}/C_{ext} and V_{CC} . The output pulse duration also can be reduced by taking \overline{CLR} low.

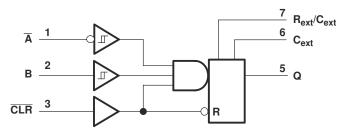
Pulse triggering occurs at a particular voltage level and is not directly related to the transition time of the input pulse. The \overline{A} and B inputs have Schmitt triggers with sufficient hysteresis to handle slow input transition rates with jitter-free triggering at the outputs.

Once triggered, the basic pulse duration can be extended by retriggering the gated low-level-active (\overline{A}) or high-level-active (B) input. Pulse duration can be reduced by taking \overline{CLR} low. \overline{CLR} can be used to override \overline{A} or B inputs. The input/output timing diagram illustrates pulse control by retriggering the inputs and early clearing.

The SN74LVC1G123 device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

7.2 Functional Block Diagram



7.3 Feature Description

This part is available in the Texas Instruments NanoFree[™] package. It supports 5-V V_{CC} operation and accepts inputs up to 5.5 V. The max t_{pd} is 8 ns at 3.3 V. It supports mixed-mode voltage operation on all ports.

Down translation can be achieved to V_{CC} from up to 5.5 V.

Schmitt-trigger circuitry on \overline{A} and B inputs allows for slow input transition rates. The device can be edge triggered from active-high or active-low gated logic inputs. It can support up to 100% duty cycle from retriggering.

Clear can be used to terminate the output pulse early.

Glitch-free power-up reset is on all outputs.

loff supports live insertion, partial-power-down mode, and back-drive protection.

Latch-up performance exceeds 100 mA per JESD 78, Class II.



7.4 Device Functional Modes

Table 7-1 lists the functional modes for the SN74LVC1G123.

Table 7-1. Function Table

INPUTS			OUTPUTS
CLR	Ā	В	Q
L	Х	Х	L
Х	Н	Х	L(1)
Х	Х	L	L(1)
Н	L	1	Л
Н	<u></u>	Н	Л
1	L	Н	Л

⁽¹⁾ These outputs are based on the assumption that the indicated steady-state conditions at the A and B inputs have been set up long enough to complete any pulse started before the setup.

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The SN74LVC1G123 can be used for many applications. The application shown here is a switch debounce circuit. Many switches produce multiple triggers when pressed, and the debounce circuit turns the many triggers into one. This circuit takes advantage of the retrigger capability of the SN74LVC1G123 in that the output pulse length only has to be longer than the longest individual bounce (typically less than 1 ms).

8.2 Typical Application

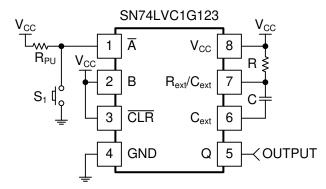


Figure 8-1. Typical Application of the SN74LVC1G123

8.2.1 Design Requirements

- 1. Recommended Input Conditions:
 - For specified high and low levels, see V_{IH} and V_{IL} in Section 5.3.
 - Inputs and outputs are overvoltage tolerant, allowing them to go as high as 4.6 V at any valid V_{CC} .
- 2. Recommended Output Conditions:
 - Load current should not exceed values listed in Section 5.3.

8.2.2 Detailed Design Procedure

The values for V_{CC}, R_{PU}, R, and C must be selected for proper operation.

V_{CC} is selected at 1.8 V. This value is usually driven by the logic voltage of the system, but is arbitrary in this case.

 R_{PII} is selected at 10 k Ω .

R and C are selected via the plots in Section 8.2.3 and are based on the time desired for the output pulse. In this case, the output pulse will be 1 ms. Since the supply voltage has been selected at 1.8 V, Figure 8-2 is used to determine the R and C values required. First convert the desired pulse width (t_w), 1 ms, to ns. This yields 10⁶ ns. Next follow that line across to see which R and C values intersect it.

R is selected at 10 k Ω because that line intersects nicely with 10⁶ ns and 10⁵ pF, making the selection of C at 0.1 μF easy.

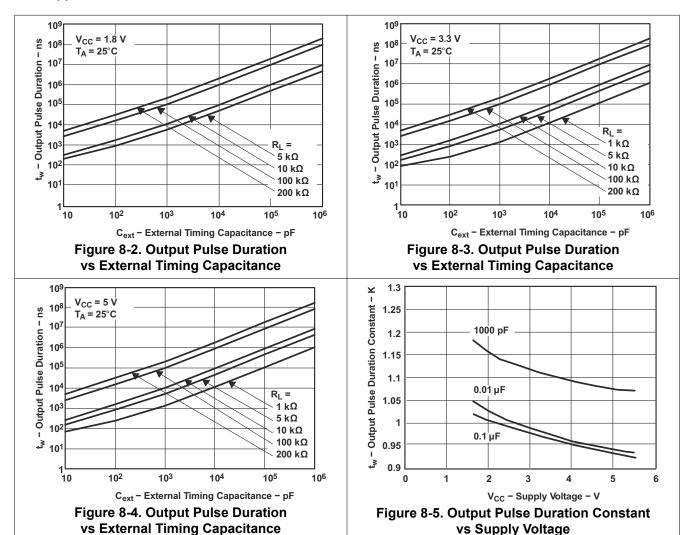


Table 8-1. Application Specific Values

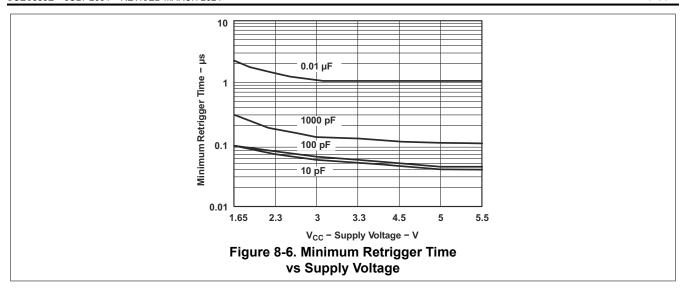
PARAMETER	VALUE
V _{CC}	1.8 V
R _{PU}	10 kΩ
t _w	1 ms
R (R _{ext})	10 kΩ
C (C _{ext})	0.1 μF

In addition to the shown components, a 0.1- μF decoupling capacitor from V_{CC} to ground should be placed as close as possible to the device.

8.2.3 Application Curves







9 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the Section 5.3.

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a $0.1-\mu F$ bypass capacitor is recommended. If multiple pins are labeled V_{CC} , then a $0.01-\mu F$ or 0.022-µF capacitor is recommended for each V_{CC} because the V_{CC} pins are tied together internally. For devices with dual-supply pins operating at different voltages, for example V_{CC} and V_{DD} , a 0.1- μ F bypass capacitor is recommended for each supply pin. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of 0.1 µF and 1 µF are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

10 Layout

10.1 Layout Guidelines

Reflections and matching are closely related to the loop antenna theory but are different enough to be discussed separately from the theory. When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self-inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. Figure 10-1 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

10.2 Layout Example

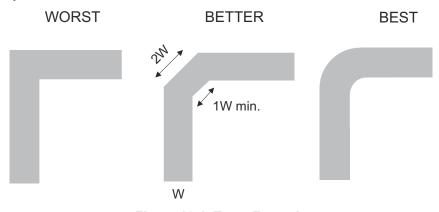


Figure 10-1. Trace Example



11 Device and Documentation Support

11.1 Documentation Support

11.1.1 Related Documentation

For related documentation see the following:

Implications of Slow or Floating CMOS Inputs, SCBA004

11.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

11.4 Trademarks

NanoFree[™] is a trademark of Texas Instruments.

TI E2E[™] is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

11.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

11.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

12 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision D (June 2015) to Revision E (March 2024)

Page

Updated format to match new TI layout and flow. Tables, figures and cross-references use a new numbering sequence throughout the document.

Changes from Revision C (October 2013) to Revision D (June 2015)

Page

- Added Applications, Device Information table, Pin Configuration and Functions section, ESD Ratings table,
 Typical Characteristics, Feature Description section, Device Functional Modes, Application and
 Implementation section, Power Supply Recommendations section, Layout section, Device and
 Documentation Support section, and Mechanical, Packaging, and Orderable Information section
- Removed duplicate Timing Requirements table6



C	hanges from Revision B (January 2007) to Revision C (October 2013)	Page
•	Updated document to new TI data sheet format	1
•	Updated Features	1
•	Updated operating temperature range	4
	Added Thermal Information table	

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

29-Feb-2024

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
74LVC1G123DCTRE4	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(2W95, C23) (R, Z)	Samples
74LVC1G123DCTRG4	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(2W95, C23) (R, Z)	Samples
74LVC1G123DCTTE4	ACTIVE	SM8	DCT	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(2W95, C23) (R, Z)	Samples
74LVC1G123DCTTG4	ACTIVE	SM8	DCT	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(2W95, C23) (R, Z)	Samples
74LVC1G123DCURE4	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C23R	Samples
74LVC1G123DCURG4	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C23R	Samples
74LVC1G123DCUTG4	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C23R	Samples
SN74LVC1G123DCTR	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(2W95, C23) (R, Z)	Samples
SN74LVC1G123DCTT	ACTIVE	SM8	DCT	8	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(2W95, C23) (R, Z)	Samples
SN74LVC1G123DCUR	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(22FT, C23Q, C23R)	Samples
SN74LVC1G123DCUT	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(C23J, C23Q, C23R)	Samples
SN74LVC1G123YZPR	ACTIVE	DSBGA	YZP	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(D87, D8N)	Samples

⁽¹⁾ The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".



PACKAGE OPTION ADDENDUM

www.ti.com 29-Feb-2024

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74LVC1G123DCURG4	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
74LVC1G123DCUTG4	VSSOP	DCU	8	250	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC1G123DCTR	SM8	DCT	8	3000	180.0	12.4	3.15	4.35	1.55	4.0	12.0	Q3
SN74LVC1G123DCTT	SM8	DCT	8	250	180.0	12.4	3.15	4.35	1.55	4.0	12.0	Q3
SN74LVC1G123DCUR	VSSOP	DCU	8	3000	178.0	9.0	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC1G123DCUT	VSSOP	DCU	8	250	178.0	9.5	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC1G123DCUT	VSSOP	DCU	8	250	178.0	9.0	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC1G123YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1



www.ti.com 11-May-2024



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74LVC1G123DCURG4	VSSOP	DCU	8	3000	202.0	201.0	28.0
74LVC1G123DCUTG4	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC1G123DCTR	SM8	DCT	8	3000	190.0	190.0	30.0
SN74LVC1G123DCTT	SM8	DCT	8	250	190.0	190.0	30.0
SN74LVC1G123DCUR	VSSOP	DCU	8	3000	180.0	180.0	18.0
SN74LVC1G123DCUT	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC1G123DCUT	VSSOP	DCU	8	250	180.0	180.0	18.0
SN74LVC1G123YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0





NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.





NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-187 variation CA.





NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.





DIE SIZE BALL GRID ARRAY



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



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